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NTE2679 Silicon NPN Transistor Power, High Voltage w/Built-In Damper Diode TO220F Type Package

Features:

- High Breakdown Voltage: $V_{CBO} = 1500V$ Min
- Wide Area of Safe Operation
- Built-In Damper Diode

Applications:

- Horizontal Deflection Output for TV or CRT Monitor

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector-Base Voltage, V_{CBO}	1500V
Collector-Emitter Voltage, V_{CEO}	1500V
Emitter-Base Voltage, V_{EBO}	5V
Collector Current, I_C	
Continuous	6A
Peak	9A
Continuous Base Current, I_B	3A
Collector Power Dissipation, P_C	
$T_A = +25^\circ C$	2W
$T_C = +25^\circ C$	30W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 500mA, I_C = 0$	5	-	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 3A, I_B = 750mA$	-	-	2.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 3A, I_B = 750mA$	-	-	1.5	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1000V, I_E = 0$	-	-	50	μA
		$V_{CB} = 1500V, I_E = 0$	-	-	1.0	mA
DC Current Gain	h_{FE}	$I_C = 3A, V_{CE} = 5V$	5	-	12	
Collector-Emitter Diode Forward Voltage	V_{ECF}	$I_F = 3A$	-	-	2.0	V
Current Gain Bandwidth Product	f_T	$I_C = 100mA, V_{CE} = 10V, f = 0.5MHz$	-	3	-	MHz
Storage Time	t_{stg}	Resistive Load	-	-	5.0	μs
Fall Time	t_f	$I_C = 3A, I_{B1} = 750mA, I_{B2} = -1.5A$	-	-	0.5	μs

